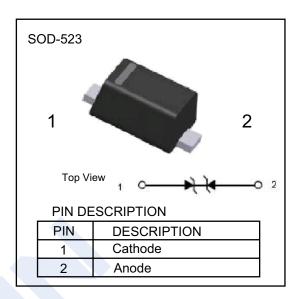
SMD Type Diodes

## TVS Diodes ESD5Z3.3C

#### ■ Features

- Low Clamping Voltage.
- Small Body Outline Dimensions..
- Low Leakage
- ESD Rating of Class 3(>16kV) per Human Body
- IEC61000-4-2 Level 4 ESD Protection IEC61000-4-4 Level 4 EFT Protection



### ■ Absolute Maximum Ratings Ta = 25°C

	Symbol	Value	Unit		
IEC 61000-4-2(ESD)	Contact		±30	KV	
	Air		±30	IXV	
IEC 61000-4-4(EFT)			40	Α	
ESD Voltage Pe		16	KV		
Total Power Dissipation on FR-4	P <sub>D</sub>	500	mW		
Junction Temperature	TJ	150			
Storage Temperature range			-55 to +150	°C	
Lead Solder Temperature - Maximum			000		
(10 Second Duration	TL	260			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

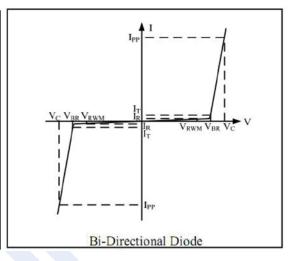
<sup>\*1.</sup> FR-4 printed circuit board, single-sided copper, mounting pad 1 cm<sup>2</sup>

Diodes **SMD** Type

### **TVS Diodes** ESD5Z3.3C

#### ■ Electrical Characteristics Ta = 25°C unless otherwise noted

Symbol	Parameter				
IPP	Maximum Reverse Peak Pulse Current				
Vc	Clamping Voltage @ I <sub>PP</sub>				
V <sub>RWM</sub>	Working Peak Reverse Voltage				
IR	Maximum Reverse Leakage Current @ V <sub>RWM</sub>				
VBR	Breakdown Voltage @ I <sub>T</sub>				
I <sub>T</sub>	Test Current				
IF	I <sub>F</sub> Forward Current				
V <sub>F</sub> Forward Voltage @ I <sub>F</sub>					
P <sub>pk</sub> Peak Power Dissipation					
C	Max. Capacitance @V <sub>B</sub> = 0 and f = 1 MHz				



Device	Marking	VRWM	I <sub>R</sub> (uA)@	V <sub>BR</sub> (V)@		V <sub>C</sub> (V)@ IPP =	vc (v) @		Ppp(W		
		(V)	VRWM	IT	IT	5.0 A	Max IPP	IPP(A)	)	C(pF)	VC
		Max	Max	Min	mA	Тур	Max	Max	Max	Тур	IEC6100-4-
ESD5Z3.3C	ZE	3.3	0.05	5.0	1.0	8.4	14.1	11.2	158	105	2

(TA=25°C unless otherwise noted. VF=1.1V Max.@IF=10mA for all types)

- 1.Surge current waveform per Figure 5.
- 2.VBR is measured with a pulse test current IT at an ambient temperature of 25 ℃
- 3. For test procedure see Fugures 3 and 4.

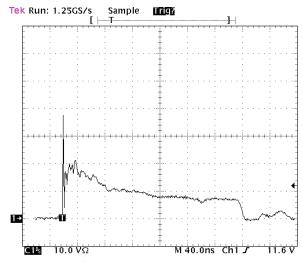
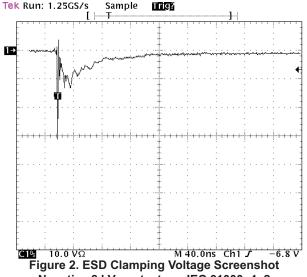


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV contact per IEC 61000-4-2



Negative 8 kV contact per IEC 61000-4-2

SMD Type Diodes

### TVS Diodes ESD5Z3.3C

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

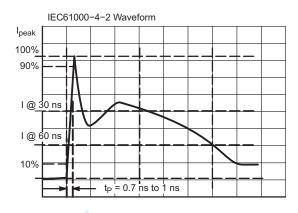
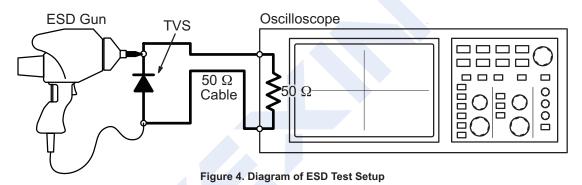


Figure 3. IEC61000-4-2 Spec



#### **ESD Voltage Clamping**

For sensitive circuit elements, it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level.

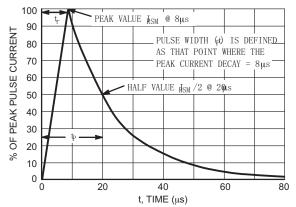
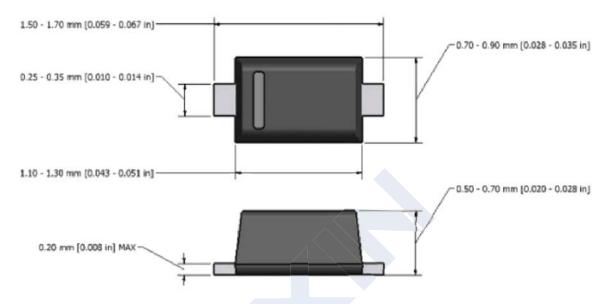


Figure 5. 8 X 20 µs Pulse Waveform

SMD Type Diodes

# TVS Diodes ESD5Z3.3C

■ Package Outline Dimensions (SOD-523)



Note: Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

■ The Recommended Mounting Pad Size

